

L Number	Hits	Search Text	DB	Time stamp
1	72524	tan(tantalum adj3 nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/03/25 12:23
2	72524	tan (tantalum adj3 nitride)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/03/25 12:23
3	3889	barrier with (ta (tan (tantalum adj3 nitride) ))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/03/25 12:24
4	4074	(conformal diffussion diffused barrier) with (ta (tan (tantalum adj3 nitride) ))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/03/25 12:25
5	2281	((conformal diffussion diffused barrier) with (ta (tan (tantalum adj3 nitride) ))) same (copper cu)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/03/25 12:26
6	1774	((conformal diffussion diffused barrier) with (ta (tan (tantalum adj3 nitride) ))) same (copper cu)) and ((integrated circuit) ic)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 12:28

ELECTROCHEMICAL TRENCH COPPER  
INSULATE SEED BARRIER LAYER

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C10D;

EPI-CODES: U11-C05C6; U11-D03B2;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2000-142190

Non-CPI Secondary Accession Numbers: N2000-354197